



Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-30V	5.7mΩ@-10V	-75A
	7.7mΩ@-4.5V	

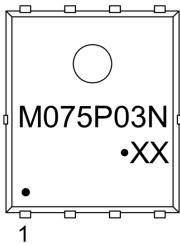
Feature

- Trench Technology Power MOSFET
- Low $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

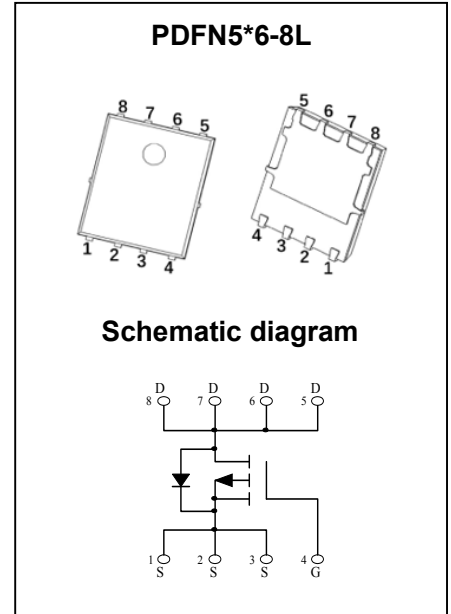
Application

- Power Switching Application

MARKING:



M075P03N = Device Code
 XX = Date Code
 •XX = Solid Dot = Green Indicator



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit	
Drain - Source Voltage	V_{DS}	-30	V	
Gate - Source Voltage	V_{GS}	±20	V	
Continuous Drain Current ¹	$T_C = 25^\circ\text{C}$	I_D	-75	A
	$T_C = 100^\circ\text{C}$	I_D	-53	A
Pulsed Drain Current ²	I_{DM}	-300	A	
Single Pulsed Avalanche Current ³	I_{AS}	23	A	
Single Pulsed Avalanche Energy ³	E_{AS}	132	mJ	
Power Dissipation ⁵	$T_C = 25^\circ\text{C}$	P_D	89	W
Thermal Resistance from Junction to Ambient ⁶	$R_{\theta JA}$	17	$^\circ\text{C}/\text{W}$	
Thermal Resistance from Junction to Case	$R_{\theta JC}$	1.4	$^\circ\text{C}/\text{W}$	
Junction Temperature	T_J	150	$^\circ\text{C}$	
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$	

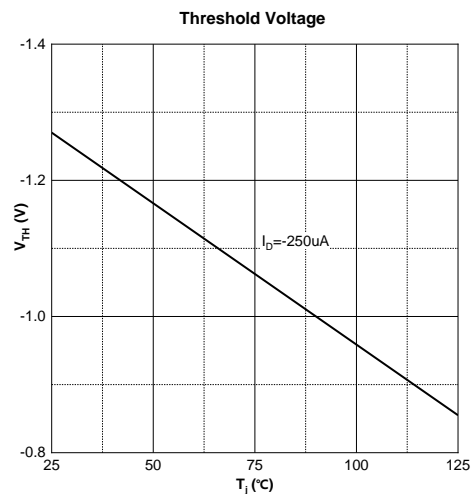
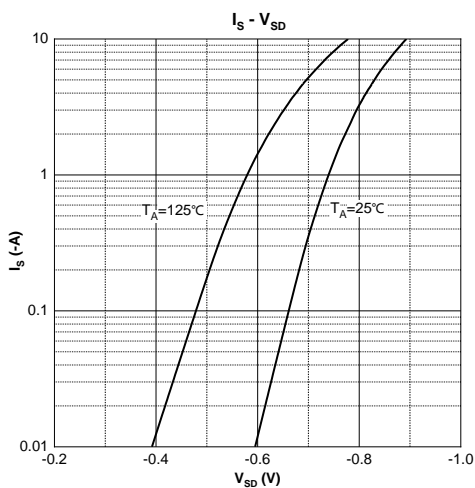
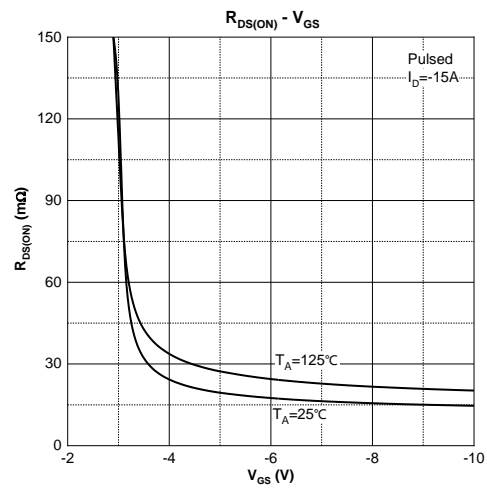
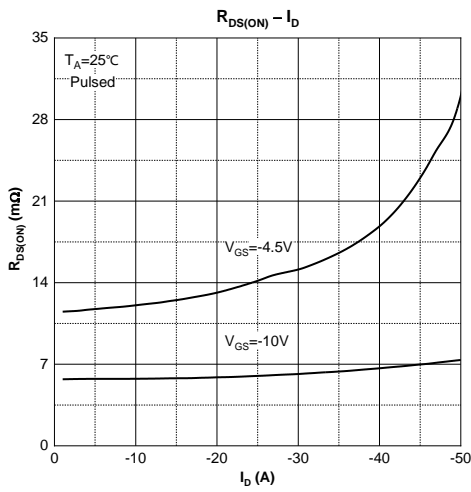
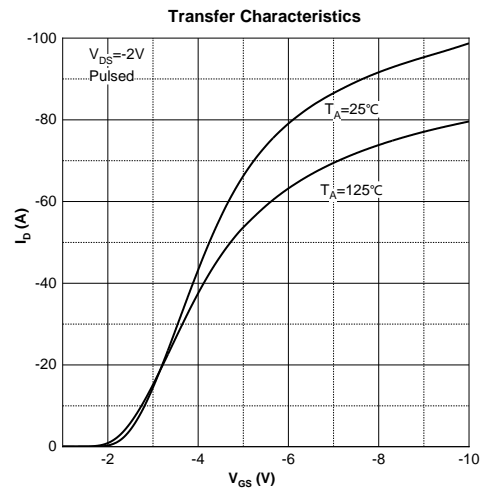
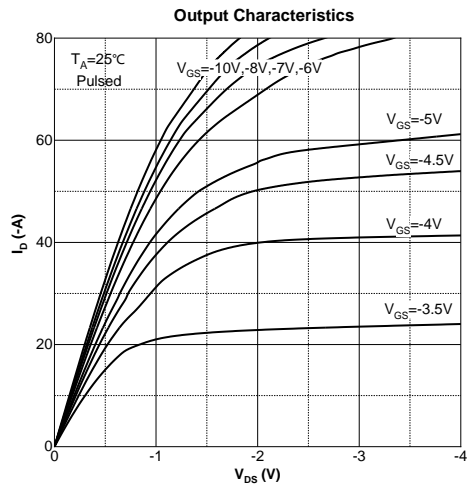
MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

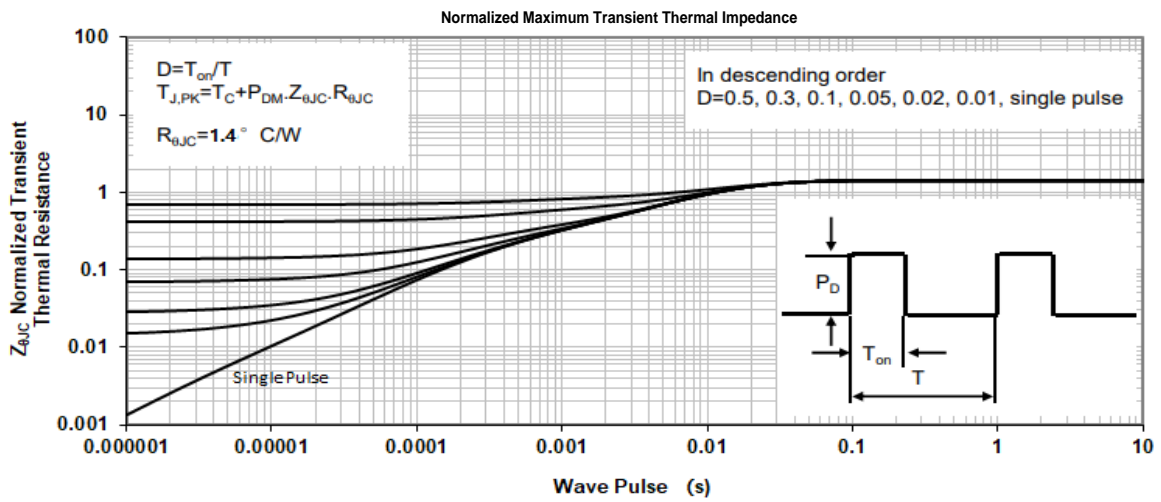
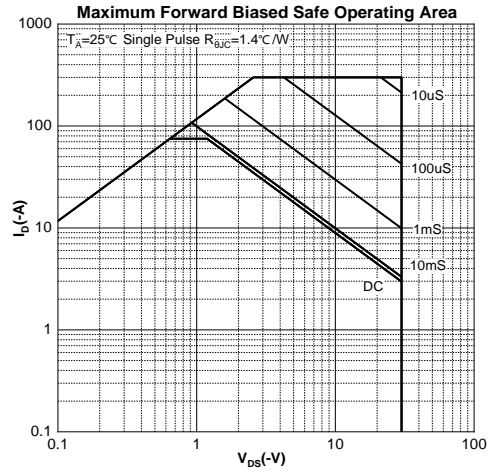
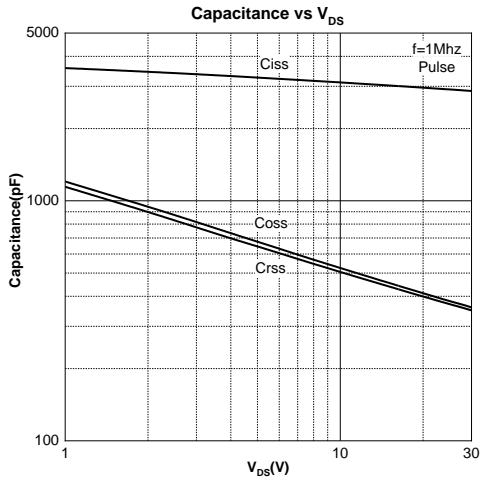
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30V, V_{GS} = 0V$			-1	μA
Gate - Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
On Characteristics⁴						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1.0	-1.2	-3.0	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -20A$		5.7	7.5	m Ω
		$V_{GS} = -4.5V, I_D = -15A$		7.7	12	
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = -15V, V_{GS} = 0V, f = 1MHz$		3062		pF
Output Capacitance	C_{oss}			459		
Reverse Transfer Capacitance	C_{rss}			441		
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		1.9		Ω
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS} = -15V, V_{GS} = -10V, I_D = -20A$		29.6		nC
Gate-source Charge	Q_{gs}			4.3		
Gate-drain Charge	Q_{gd}			11.3		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = -15V, V_{GS} = -10V,$ $R_L = 0.75\Omega, R_G = 3\Omega$		15		ns
Turn-on Rise Time	t_r			73		
Turn-off Delay Time	$t_{d(off)}$			122		
Turn-off Fall Time	t_f			75		
Source - Drain Diode Characteristics						
Diode Forward Voltage ⁴	V_{SD}	$V_{GS} = 0V, I_S = -20A$			1.2	V

Notes :

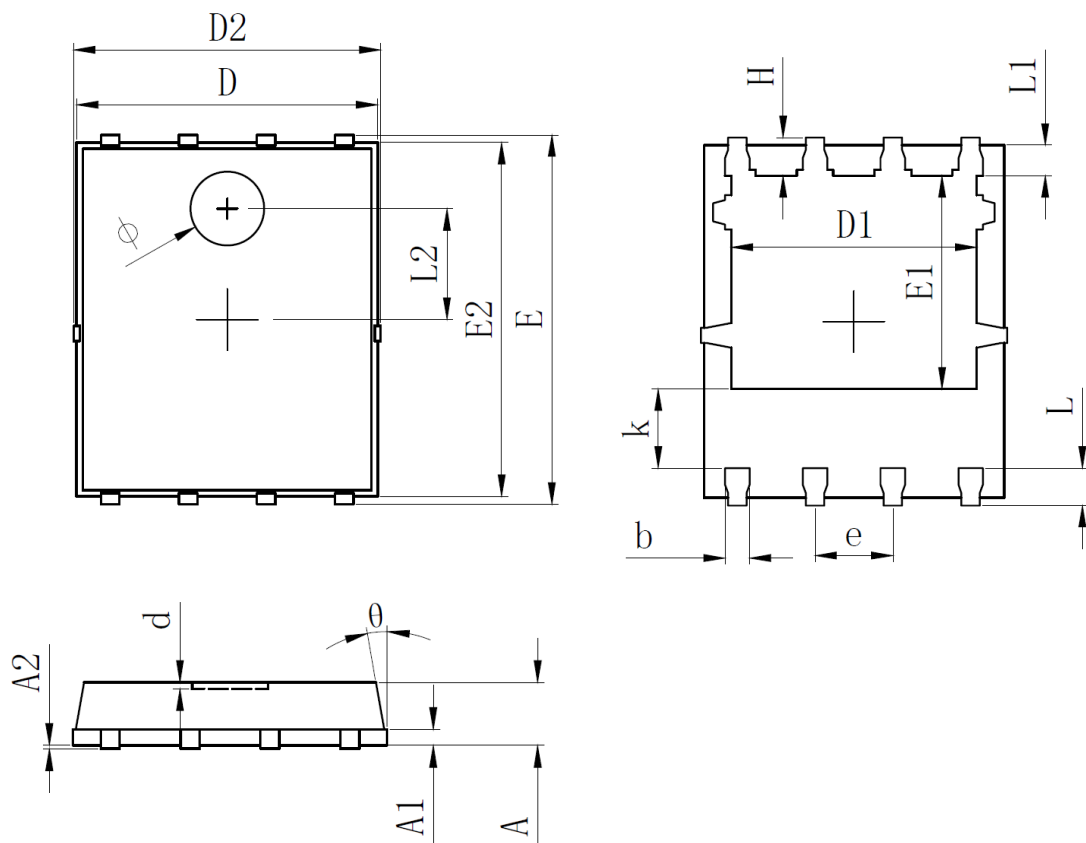
- 1.The maximum current rating is limited by package.And device mounted on a large heatsink
- 2.Pulse Test : Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
- 3.EAS condition: $V_{DD} = -25V, V_{GS} = -10V, L = 0.5mH, R_G = 25\Omega$ Starting $T_J = 25^\circ\text{C}$.
- 4.Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 5.The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ\text{C}$.And device mounted on a large heatsink
- 6.Device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

Typical Characteristics





PDFN5×6-8L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.254REF		0.010REF	
A2	0.000	0.050	0.000	0.002
D	4.824	4.976	0.190	0.196
D1	3.910	4.110	0.154	0.162
D2	4.924	5.076	0.194	0.200
E	5.924	6.076	0.233	0.239
E1	3.375	3.575	0.133	0.141
E2	5.674	5.826	0.223	0.229
b	0.350	0.450	0.014	0.018
e	1.270TYP		0.050TYP	
L	0.534	0.686	0.021	0.027
L1	0.424	0.576	0.017	0.023
k	1.190	1.390	0.047	0.055
H	0.549	0.701	0.022	0.028
θ	8°	12°	8°	12°
Φ	1.100	1.300	0.043	0.051
d	-	0.100	-	0.004